

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L13	2014	257/750	US-PGPUB; USPAT; USOCR	OR	OFF	2006/10/11 17:35
L14	2956	257/751	US-PGPUB; USPAT; USOCR	OR	OFF	2006/10/11 17:35
L15	9211	seed and barrier and (edge or periphery or peripheral)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/10/11 17:36
L16	23353	semiconductor and trench and (edge or periphery or peripheral)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/10/11 17:37
L17	808	257/622	US-PGPUB; USPAT; USOCR	OR	OFF	2006/10/11 17:39
L18	35800	l16 abd l17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:39
L19	185	l16 and l17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:42
L20	174	438/958	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:42
L21	290	438/298	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:42
L22	2270	257/734	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:43

## EAST Search History

L23	6364	semiconductor same trench and trench same edge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:46
L24	4844	semiconductor same trench and trench with edge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:46
L25	4249	semiconductor with trench and trench with edge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:46
L26	2545	semiconductor with trench and trench with edge and trench with surface and trench with between	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:47
L27	274	semiconductor with trench and trench with edge and trench with surface and trench with between with conductivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 17:48